# **DISCRETE SEMICONDUCTORS**

# DATA SHEET

# BYC8B-600 Rectifier diode Freewheeling and power factor correction

Product specification
File under Discrete Semiconductors, SC02

October 1997





# Rectifier diode Freewheeling and power factor correction

**BYC8B-600** 

# **GENERAL DESCRIPTION**

Glass passivated, epitaxial rectifier diode in a plastic envelope suitable for surface mounting. This diode has extremely fast reverse recovery time and low reverse recovery current and is designed specifically for use in forced commutation applications, for example:- as the output rectifier diode in power factor correction circuits operating in continuous conduction mode; or as a freewheeling diode in half-bridge and full-bridge switched mode power supplies.

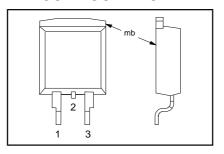
## **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
I <sub>F(AV)</sub> V <sub>RRM</sub> V <sub>F</sub> t <sub>rr</sub> I <sub>rrm</sub>	Average forward current Repetitive peak reverse voltage Forward voltage Reverse recovery time Reverse recovery current	19	8 600 1.85 12	A V V ns A

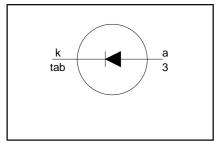
# **PINNING - SOT404**

PIN	DESCRIPTION	
1	no connection	
2	cathode	
3	anode	
mb	cathode	

# **PIN CONFIGURATION**



# **SYMBOL**



# **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	Repetitive peak reverse voltage		-	600	V
V <sub>RWM</sub>	Crest working reverse voltage		-	600	V
V <sub>R</sub>	Continuous reverse voltage	$T_{mb} \le 110  ^{\circ}C^1$	-	500	V
I <sub>F(AV)</sub>	Average forward current	$\delta = 0.5$ : with reapplied $V_{\text{RRM}(mov)}$ :	-	8	Α
, ,		$T_{mb} \le 82  ^{\circ}C^{1}$			
I <sub>F(RMS)</sub>	RMS forward current	·	-	11.3	Α
I <sub>FRM</sub>	Repetitive peak forward current	$\delta$ = 0.5; with reapplied $V_{RRM(max)}$ ;	-	16	Α
		$T_{mb} \le 82  ^{\circ}C^{1}$			
I <sub>FSM</sub>	Non-repetitive peak forward	t = 10 ms	-	55	A
	current.	t = 8.3 ms	-	60	A
		sinusoidal; T <sub>i</sub> = 150°C prior to surge			
		with reapplied V <sub>RWM(max)</sub>			
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t = 10 ms	-	15	A <sup>2</sup> s
T <sub>stg</sub>	Storage temperature		-40	150	,C
T <sub>j</sub>	Operating junction temperature		-	150	°C

<sup>1</sup> Maximum mounting base temperature limited by thermal runaway.

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# THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub>	Thermal resistance junction to		-	-	2.2	K/W
R <sub>th j-a</sub>	mounting base Thermal resistance junction to ambient	minimum footprint, FR4 board	-	50	-	K/W

# STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>F</sub>	Forward voltage	I <sub>F</sub> = 8 A; T <sub>i</sub> = 150°C	-	1.4	1.85	V
	_	$I_{\rm F} = 16  {\rm A};  T_{\rm i} = 150  {\rm C}$	-	1.7	2.3	V
		$I_{\rm F} = 8 \text{ A};$	-	2.0	2.8	V
l I <sub>R</sub>	Reverse current	$\dot{V}_{R} = 600 \text{ V}$	-	9	150	μΑ
		$V_{R} = 500 \text{ V}; T_{j} = 100 \text{ °C}$	-	1.1	3.0	mΑ

# **DYNAMIC CHARACTERISTICS**

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
t <sub>rr</sub>	Reverse recovery time	$I_F = 8 \text{ A to V}_R = 400 \text{ V};$	-	19	-	ns
t <sub>rr</sub>	Reverse recovery time	$dI_F/dt = 500 \text{ Å/µs}$ $I_F = 8 \text{ A to V}_R = 400 \text{ V};$	-	32	40	ns
I <sub>rrm</sub>	Peak reverse recovery current	$dI_F/dt = 500 \text{ Å/}\mu\text{s}; T_j = 125 ^{\circ}\text{C}$ $I_F = 8 \text{ A to } V_R = 400 \text{ V};$ $dI_F/dt = 500 \text{ Å/}\mu\text{s}; T_i = 125 ^{\circ}\text{C}$	-	9.5	12	Α
$V_{fr}$	Forward recovery voltage	$I_F = 10 \text{ A; } dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	8	10	V

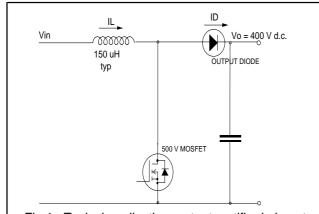


Fig.1. Typical application, output rectifier in boost converter power factor correction circuit. Continuous conduction, mode where the transistor turns on whilst forward current is still flowing in the diode.

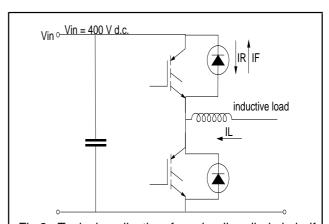


Fig.2. Typical application, freewheeling diode in half bridge converter. Continuous conduction mode, where each transistor turns on whilst forward current is still flowing in the other bridge leg diode.

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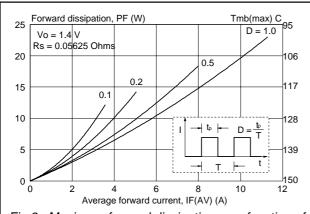


Fig.3. Maximum forward dissipation as a function of average forward current; rectangular current waveform where  $I_{F(AV)} = I_{F(RMS)} x \sqrt{D}$ .

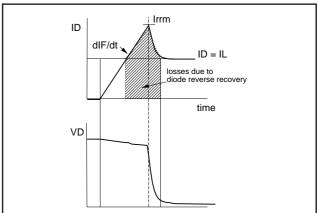


Fig.6. Origin of switching losses in transistor due to diode reverse recovery.

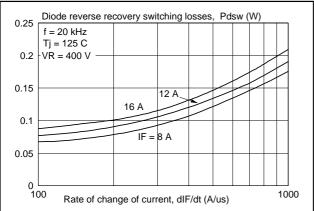


Fig.4. Typical reverse recovery switching losses in diode, as a function of rate of change of current dl<sub>r</sub>/dt.

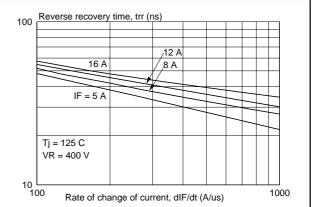


Fig.7. Typical reverse recovery time t<sub>rr</sub>, as a function of rate of change of current dl<sub>r</sub>/dt.

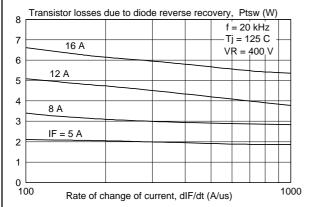


Fig.5. Typical switching losses in transistor due to reverse recovery of diode, as a function of of change of current dl<sub>F</sub>/dt.

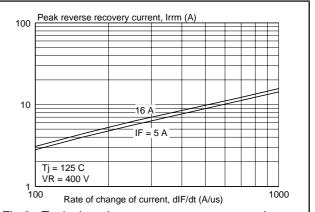
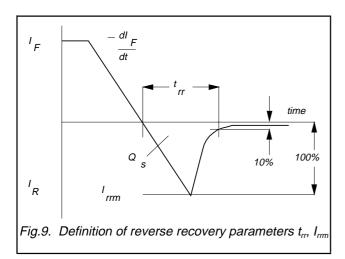


Fig.8. Typical peak reverse recovery current,  $I_{rrm}$  as a function of rate of change of current  $dI_r/dt$ .

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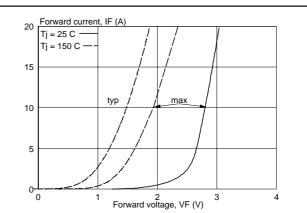


Fig.12. Typical and maximum forward characteristic  $I_{F} = f(V_{F}); T_{i} = 25^{\circ}C \text{ and } 150^{\circ}C.$ 

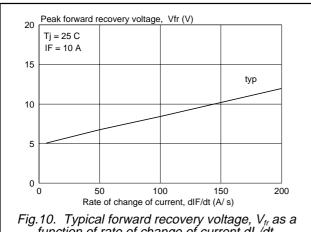


Fig.10. Typical forward recovery voltage,  $V_{\rm fr}$  as a function of rate of change of current  $dl_{\rm F}/dt$ .

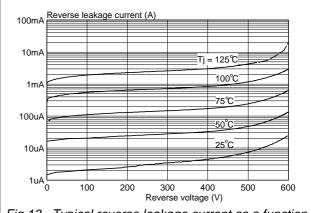
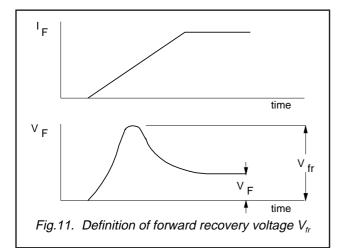


Fig.13. Typical reverse leakage current as a function of reverse voltage.  $I_R = f(V_R)$ ; parameter  $T_j$ 



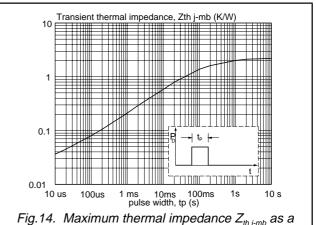
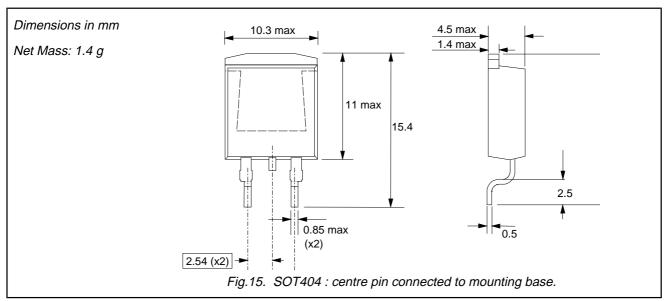


Fig.14. Maximum thermal impedance  $Z_{th j-mb}$  as a function of pulse width.

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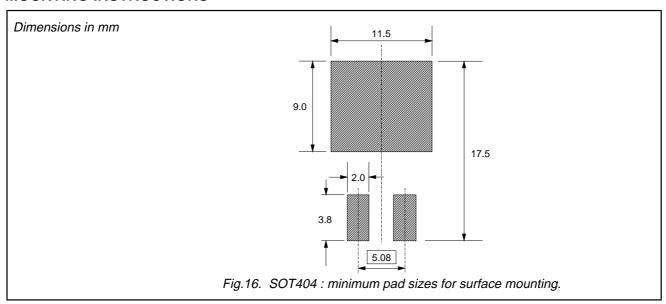
# **MECHANICAL DATA**



#### Notes

1. Epoxy meets UL94 V0 at 1/8".

# **MOUNTING INSTRUCTIONS**



#### Notes

1. Plastic meets UL94 V0 at 1/8".

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#### **DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Product specification	This data sheet contains final product specifications.

#### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

## **Application information**

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